

APPLICATION NO. 10/811056

February 23, 2005

YR

CLMPTO

1. (Currently Amended) A semiconductor device comprising:  
a first insulating film on a silicon substrate; and  
a second insulating film on said first insulating film, wherein  
said first insulating film is a silicon oxide film having a film thickness of not exceeding 1 nm-or-less and a suboxide content of not exceeding 30%-or-less; and  
said second insulating film is a high dielectric constant insulating film.
2. (Currently Amended) The semiconductor device according to claim 1, wherein  
said high dielectric constant insulating film is selected from the group consisting of a metal oxide film-or and a metal silicate film.
3. (Currently Amended) The semiconductor device according to claim 2, wherein  
said metal oxide film is an oxide film-of including at least one metal selected from-a the  
group consisting of hafnium, zirconium, lanthanum, and yttrium.
4. (Currently Amended) The semiconductor device according to claim 2, wherein  
said metal silicate film is a silicate film-of including at least one metal selected from-a the  
group consisting of hafnium, zirconium, lanthanum, yttrium, and aluminum.
5. (Original) The semiconductor device according to claim 4, wherein said metal  
silicate film contains nitrogen.
6. (Currently Amended) A semiconductor device comprising:  
a first insulating film on a silicon substrate; and  
a second insulating film on said first insulating film, wherein  
said first insulating film is a silicon oxynitride film having a film thickness-of  
not exceeding 1 nm-or-less and a suboxide content-of not exceeding 30%-or-less; and  
said second insulating film is a high dielectric constant insulating film.
7. (Currently Amended) The semiconductor device according to claim 6, wherein  
said high dielectric constant insulating film is selected from the group consisting of a metal oxide film-or and a metal silicate film.

8. (Currently Amended) The semiconductor device according to claim 7, wherein said metal oxide film is an oxide film ~~of~~ including at least one metal selected from ~~a~~ the group consisting of hafnium, zirconium, lanthanum, and yttrium.

9. (Currently Amended) The semiconductor device according to claim 7, wherein said metal silicate film is a silicate film ~~of~~ including at least one metal selected from ~~a~~ the group consisting of hafnium, zirconium, lanthanum, yttrium, and aluminum.

10. (Original) The semiconductor device according to claim 9, wherein said metal silicate film contains nitrogen.

11. (Currently Amended) A semiconductor device comprising:  
a first insulating film on a silicon substrate; and  
a second insulating film on said first insulating film, wherein  
said first insulating film is a silicon nitride film having a ~~film~~ thickness ~~of~~ not  
exceeding 1 nm ~~or less~~ and an oxygen content ~~of less than~~ not exceeding 0.1 atom%; and  
said second insulating film is a high dielectric constant insulating film.

CLAIMS 12-23 (CANCELLED)